

**Amendments to the Claims:**

This listing of claims will replace the listing of claims, as filed and as amended in the First Preliminary Amendment, in the application:

**Listing of Claims:**

Claim 1 (original): A method of removing an organic light-emitting material from defined areas of a substrate comprising the steps of arranging a shadow mask to overlie the organic material other than in the defined areas, and applying a beam of ions to the defined areas through the mask.

Claim 2 (original): A method according to claim 1, wherein the organic light-emitting material is polymeric.

Claims 3-12 (canceled).

Claim 13 (new): A method according to claim 2, wherein at least one of the mask and the substrate has recesses in its surface facing the other of the mask and the substrate.

Claim 14 (new): A method according to claim 13, wherein the ions are chemically reactive with the organic material to be etched.

Claim 15 (new): A method according to claim 14, wherein the ions are ions of a normally inert gas.

Claim 16 (new): A method according to claim 15, wherein the ions are Argon ions.

Claim 17 (new): A method according to claim 16, wherein the step of applying the beam of ions is carried out in a chamber having dimensions, at a pressure at which the mean free path of the ions is greater than or equivalent to the chamber dimensions.

Claim 18 (new): A method according to claim 17, wherein the step of applying the beam of ions is carried out at a pressure less than  $5 \times 10^{-4}$  mbar.

Claim 19 (new): A method according to claim 18, wherein the organic material is formed from an organic layer of an array of organic light emitting diodes on the substrate.

Claim 20 (new): A method according to claim 19, wherein the organic material to be removed covers a bond pad region of the substrate.

Claim 21 (new): A method according to claim 1, wherein at least one of the mask and the substrate has recesses in its surface facing the other of the mask and the substrate.

Claim 22 (new): A method according to claim 1, wherein the ions are chemically reactive with the organic material to be etched.

Claim 23 (new): A method according to claim 1, wherein the ions are ions of a normally inert gas.

Claim 24 (new): A method according to claim 23, wherein the ions are Argon ions.

Claim 25 (new): A method according to claim 1, wherein the step of applying the beam of ions is carried out in a chamber having dimensions, at a pressure at which the mean free path of the ions is greater than or equivalent to the chamber dimensions.

Claim 26 (new): A method according to claim 1, wherein the step of applying the beam of ions is carried out at a pressure less than  $5 \times 10^{-4}$  mbar.

Claim 27 (new): A method according to claim 1, wherein the organic material is formed from an organic layer of an array of organic light emitting diodes on the substrate.

Claim 28 (new): A method according to claim 27, further comprising the step of removing organic material from a least one organic light emitting diode pixel of the array of organic light emitting diodes.

Claim 29 (new): A method according to claim 1, wherein the organic material to be removed covers a bond pad region of the substrate.

Claim 30 (new): A method according to claim 1, further comprising the step of using the beam of ions to remove a layer of electrically conducting polymeric material in the defined areas.